DISCRETE SEMICONDUCTORS

DATA SHEET

PEMH4; PUMH4 NPN/NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = open

Product data sheet Supersedes data of 2003 Oct 02 2004 Apr 14



NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = open

PEMH4; PUMH4

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	NPN	_	_	_
R1	bias resistor	10	_	kΩ
R2	bias resistor	open	_	_

QUICK REFERENCE DATA

DESCRIPTION

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE ⁽¹⁾	NPN/PNP	PNP/PNP
TIPE NOWIBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMH4	SOT666	-	H4	PEMD4	PEMB4
PUMH4	SOT363	SC-88	H*4	PUMD4	PUMB4

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
TIPE NUMBER	SIMPLIFIED OUTLINE AND STIMBOL	PIN	DESCRIPTION	
PEMH4	□	1	emitter TR1	
PUMH4		2	base TR1	
		3	collector TR2	
		4	emitter TR2	
	TR1	5	base TR2	
	R1	6	collector TR1	
	1 2 3			
	Top view MAM453			

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
NAME		DESCRIPTION	VERSION
PEMH4	_	 Plastic surface mounted package; 6 leads 	
PUMH4	1	Plastic surface mounted package; 6 leads	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transistor							
V _{CBO}	collector-base voltage	open emitter	_	50	V		
V _{CEO}	collector-emitter voltage	open base	-	50	V		
V _{EBO}	emitter-base voltage	open collector	_	5	V		
Io	output current (DC)		-	100	mA		
I _{CM}	peak collector current		_	100	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C					
	SOT363	note 1	_	200	mW		
	SOT666	notes 1 and 2	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		-	150	°C		
T _{amb}	operating ambient temperature		-65	+150	°C		
Per device	•				•		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C					
	SOT363	note 1	_	300	mW		
ı	SOT666	notes 1 and 2	_	300	mW		

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Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor							
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA		
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	1	μΑ		
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ		
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA		
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	_	_			
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	-	150	mV		
R1	input resistor		7	10	13	kΩ		
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	_	2.5	pF		

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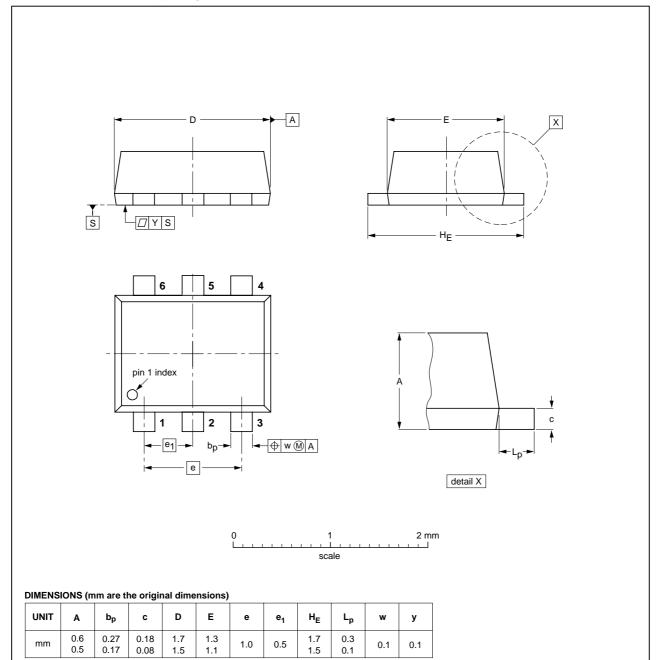
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PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT666						-04-11-08- 06-03-16

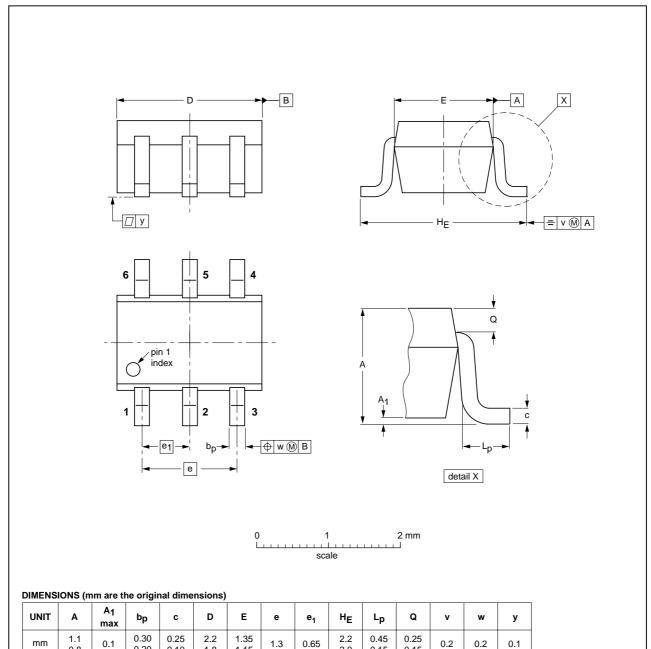
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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = open

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Plastic surface-mounted package; 6 leads

SOT363



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT363			SC-88			04-11-08 06-03-16

0.15

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0.10

1.15

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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